

05-10-04



Docket No.: 384848011US
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Peng et al.

Application No.: 10/765,802

Confirmation No.: 2492

Filed: January 26, 2004

Art Unit: 2818

For: HIGH DENSITY SEMICONDUCTOR
MEMORY CELL AND MEMORY ARRAY
USING A SINGLE TRANSISTOR AND
HAVING VARIABLE GATE OXIDE
BREAKDOWN

Examiner: Not Yet Assigned

INFORMATION DISCLOSURE STATEMENT (IDS)

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 CFR 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO/SB/08. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is filed before the mailing date of a first Office Action on the merits as far as is known to the undersigned (37 CFR 1.97(b)(3)).

A summary/abstract translation of the non-English language references is enclosed.

A copy of only those references listed below is attached:

For. Doc No.	Ctry	Patentee/Applicant	Publication Date
61292295	JP	Fujitsu Ltd.	December 23, 1986
0 295 935	EP	Advanced Micro Devices,	December 21, 1988

Other Documents
WU, E.W. et al; Voltage-Dependent Voltage-Acceleration of Oxide
SUNE, JORDI et al; Post Soft Breakdown Conduction in SiO ₂ Gate
DeGRAAF, C., et al, A Novel High-Density Low-Cost Diode
RASRAS, MAHMOUD et al; Substrate Hole Current Origin After Oxide
LOMBARDO, S. et al; Softening of Breakdown in Ultra-Thin Gate Oxide
MIRANDA, ENRIQUE et al; Analytic Modeling of Leakage Current

The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 50-0665, under Order No. 384848011US.

Dated: 5/7/04

Respectfully submitted,

By 

Chun M. Ng

Registration No.: 36,878

PERKINS COIE LLP

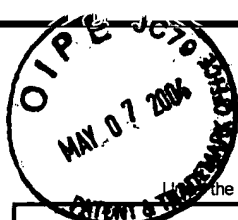
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PTO/SB/08a/b (08-03)

Approved for use through 07/31/2006. OMB 0651-0031

U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

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Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>				Complete if Known	
				Application Number	10/765,802-Conf. #2492
				Filing Date	January 26, 2004
				First Named Inventor	Jack Z. Peng
				Art Unit	2818
				Examiner Name	Not Yet Assigned
Sheet	1	of	3	Attorney Docket Number	384848011US

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Examiner Signature		Date Considered	
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Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>				Complete if Known	
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				First Named Inventor	Jack Z. Peng
				Art Unit	2818
				Examiner Name	Not Yet Assigned
				Attorney Docket Number	384848011US
Sheet	2	of	3		

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FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	MM-DD-YYYY			
		JP-61292295	12-23-1986	Fujitsu Ltd.		
		EP-0 295 935	12-21-1988	Advanced Micro Devices, Inc.		

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. **CITE NO.: Those patent(s) or publication(s) which are marked with an double asterisk (**) next to the Cite No. are not supplied because they were previously cited by or submitted to the Office in a prior application relied upon in this application for an earlier filing date under 35 U.S.C. 120. ¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		WU, E.W. et al; Voltage-Dependent Voltage-Acceleration of Oxide Breakdown for Ultra-Thin Oxides; IEEE, 2000.	
		SUNE, JORDI et al; Post Soft Breakdown Conduction in SiO2 Gate Oxides; IEEE, 2000.	
		DeGRAAF, C., et al, A Novel High-Density Low-Cost Diode Programmable Read Only Memory, IEEE, 1996.	
		RASRAS, MAHMOUD et al; Substrate Hole Current Origin After Oxide Breakdown; IEEE, 2000.	
		LOMBARDO, S. et al; Softening of Breakdown in Ultra-Thin Gate Oxide nMOSFET's at Low Inversion Layer Density; 39th Annual International Reliability Physics Symposium; Orlando, FL 2001.	

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		MIRANDA, ENRIQUE et al; Analytic Modeling of Leakage Current Through Multiple Breakdown Paths in SiO ₂ Films; 39th Annual International Reliability Physics Symposium; Orlando, FL 2001.	

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